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## ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises an impurity diffusion layer formed on a semiconductor substrate, an insulating film for covering the impurity diffusion layer, a capacitor formed on the insulating film consisting of a lower electrode, an oxide dielectric film, and an upper electrode, an interlayer insulating film for covering the capacitor, two opening portions formed in the interlayer insulating film to expose the impurity diffusion layer and the upper electrode, a local interconnection formed in two opening portions, and on the interlayer insulating film in a range containing at least a region where the upper electrode oxide film. contacts the dielectric and another interlayer insulating films for covering the local interconnection.